## 2SK3047

## Silicon N-channel power MOSFET

#### ■ Features

• Avalanche energy capability guaranteed: EAS > 15 mJ

 $\bullet$  Gate-source surrender voltage  $V_{GSS}$ :  $\pm 30 \text{ V}$  guaranteed

• High-speed switching

• No secondary breakdown

#### ■ Applications

- Non-contact relay
- · Solenoid drive
- Motor drive
- Control equipment
- Switching mode regulator

#### ■ Absolute Maximum Ratings $T_C = 25$ °C

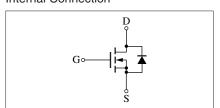
Parameter	Symbol	Rating	Unit	
Drain-source surrender voltage	V <sub>DSS</sub>	800	V	
Gate-source surrender voltage	V <sub>GSS</sub>	±30	V	
Drain current	$I_{\mathrm{D}}$	±2	A	
Peak drain current	$I_{\mathrm{DP}}$	±4	A	
Avalanche energy capability *	EAS	15	mJ	
Power dissipation	$P_{\mathrm{D}}$	30	W	
$T_a = 25^{\circ}C$		2		
Channel temperature	T <sub>ch</sub>	150	°C	
Storage temperature	$T_{stg}$	-55 to +150	°C	

Note) \*: L = 7.5 mH,  $I_L = 2 A$ , 1 pulse

### Unit: mm 4.6±0.2 9.9±0.3 2.9±0.2 φ 3.2±0.1 15.0±0.5 1.4±0.2 2.6±0.1 1.6±0.2 13.7±0.2 0.55±0.15 5.08±0.50 1: Gate 2: Drain 3: Source TO-220D-A1 Package

Marking Symbol: K3047

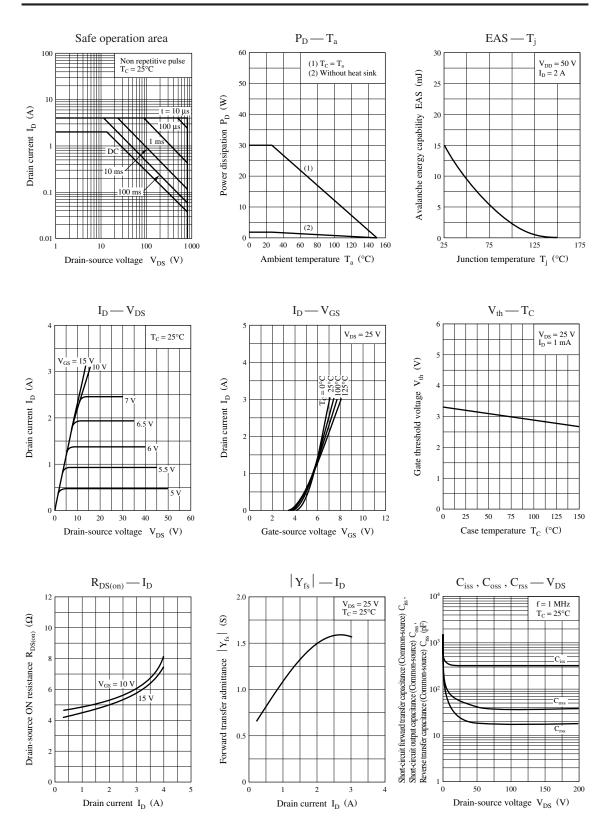
#### Internal Connection

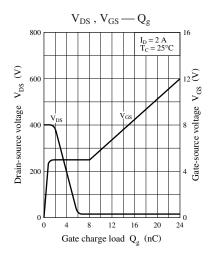


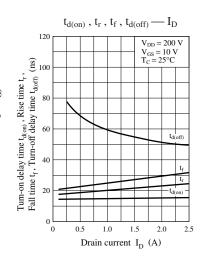
### ■ Electrical Characteristics $T_C = 25$ °C $\pm 3$ °C

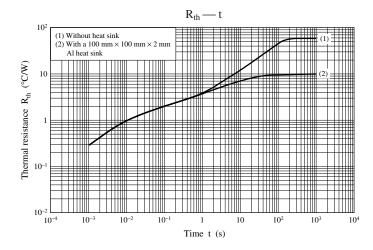
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source surrender voltage	V <sub>DSS</sub>	$I_D = 1 \text{ mA}, V_{GS} = 0$	800			V
Drain-source cutoff current	$I_{DSS}$	$V_{DS} = 640 \text{ V}, V_{GS} = 0$			100	μΑ
Gate-source cutoff current	$I_{GSS}$	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$			±1	μΑ
Gate threshold voltage	V <sub>th</sub>	$V_{DS} = 25 \text{ V}, I_{D} = 1 \text{ mA}$	2.0		5.0	V
Forward transfer admittance	Y <sub>fs</sub>	$V_{DS} = 25 \text{ V}, I_D = 1 \text{ A}$	0.7	1.1		S
Drain-source ON resistance	R <sub>DS(on)</sub>	$V_{GS} = 10 \text{ V}, I_D = 1 \text{ A}$		4.8	7.0	Ω
Diode forward voltage	$V_{\mathrm{DF}}$	$I_{DR} = 2 A, V_{GS} = 0$			-1.3	V
Short-circuit forward transfer capacitance (Common source)	C <sub>iss</sub>	$V_{DS} = 20 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$		350		pF
Short-circuit output capacitance (Common source)	C <sub>oss</sub>			60		pF
Reverse transfer capacitance (Common source)	C <sub>rss</sub>			25		pF
Turn-on delay time	t <sub>d(on)</sub>	$V_{DD} = 200 \text{ V}, I_D = 1 \text{ A}, R_L = 200 \Omega$		15		ns
Rise time	t <sub>r</sub>	$V_{GS} = 10 \text{ V}$		20		ns
Fall time	$t_{\rm f}$			25		ns
Turn-off delay time	t <sub>d(off)</sub>			60		ns
Thermal resistance (ch-c)	R <sub>th(ch-c)</sub>				4.1	°C/W
Thermal resistance (ch-a)	R <sub>th(ch-a)</sub>				62.5	°C/W

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.









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